

IN THE ABSTRACT:

Replace the Abstract currently of record with the enclosed new Abstract of the Disclosure.

IN THE SPECIFICATION:

Please amend the specification as follows:

Please amend the paragraph on page 48, lines 7-13 with the following rewritten paragraph:

B' Next, on the resulting SOS substrate, using a CMOS process, an n-type MOSFET of gate 17 width 50 microns and gate 17 length 0.8 micron was produced. A sectional diagram of the device is shown in Fig. 4. In this case, LOCOS (Local Oxidation) 19 was used for device separation, and thickness of gate oxide film 15 was 8 nm. To the channel 10,  $\text{BF}_2^+$  at energy 35 keV was implanted in an amount of  $6.0 \times 10^{12}/\text{cm}^2$ .

Please amend the paragraph beginning on page 48, line 26 to page 49, line 9 with the following rewritten paragraph:

Yet further, a photodiode was produced on the resulting SOS substrate. A sectional diagram of the device is shown in Fig. 7.

B2 The device was formed in a p-i-n structure in the horizontal direction of the substrate 1, the size of the i-type area 21 was length 75 micron and width 1 micron. To the n-type area 20, As+

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B2  
at energy 35 keV of  $2.0 \times 10^{15}/\text{cm}^2$  was implanted. Further, to the p-type area 22,  $\text{BF}_2^+$  at energy 35 keV of  $2.0 \times 10^{15}/\text{cm}^2$  was implanted. When a 2V bias is applied to the n-type area, dark current was  $2.7 \times 10^{-12}$  A, photocurrent under light irradiation of intensity  $1\text{W}/\text{cm}^2$  at wavelength 850 nm was  $4.8 \times 10^{-10}$  A.

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